

FIG. 1

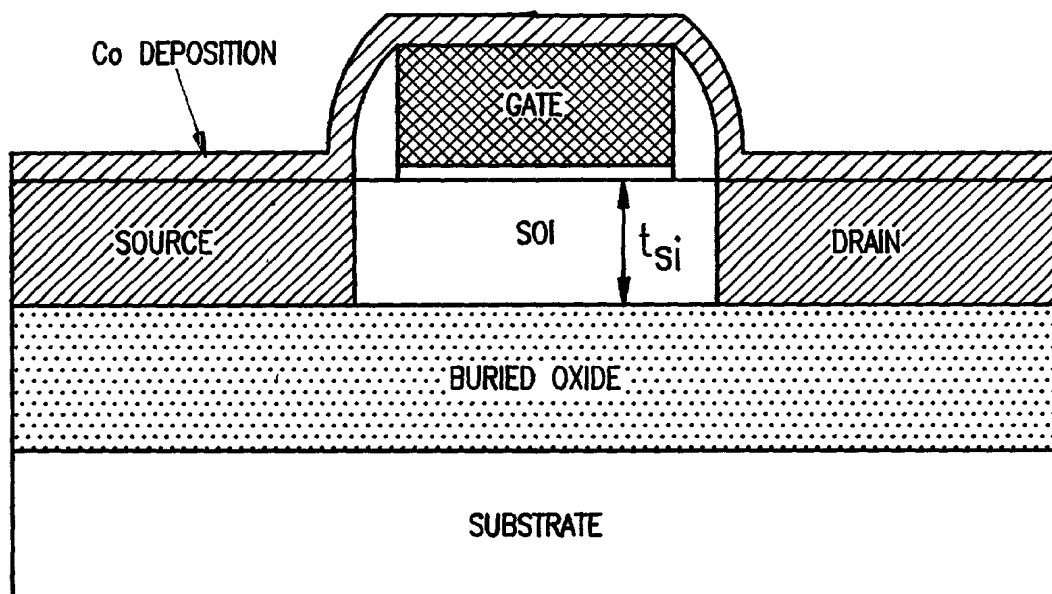


FIG. 2

FIG. 1

FORM  $\text{Co}_2\text{Si}$  BY LOW TEMPERATURE ANNEAL

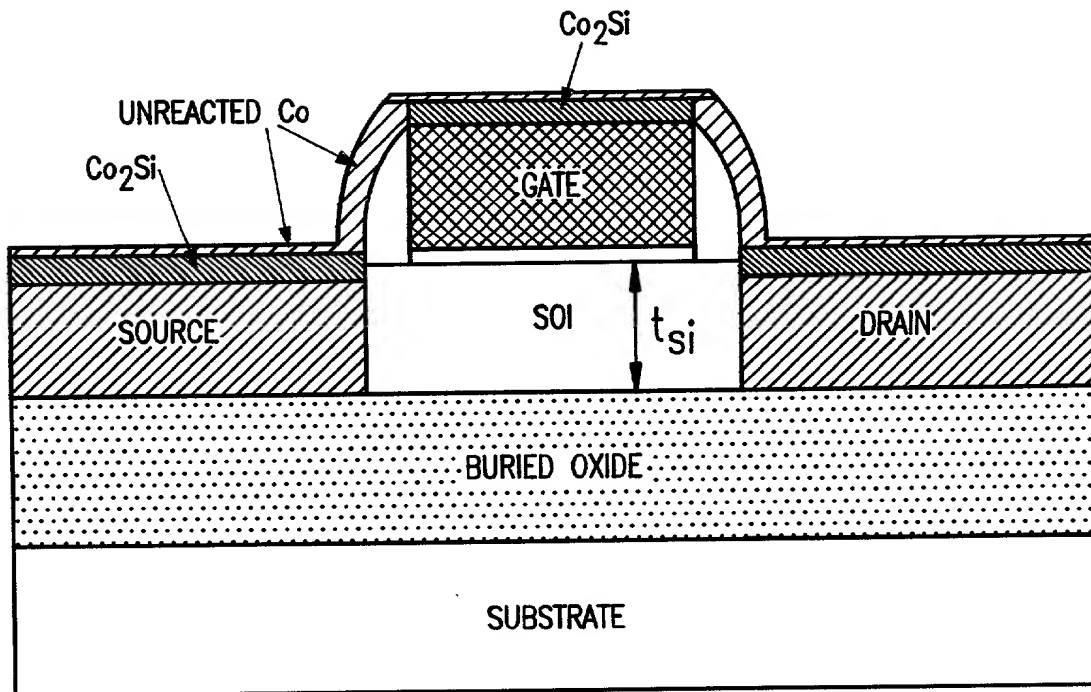


FIG.3

DEPOSITE  $\alpha\text{-Si}$

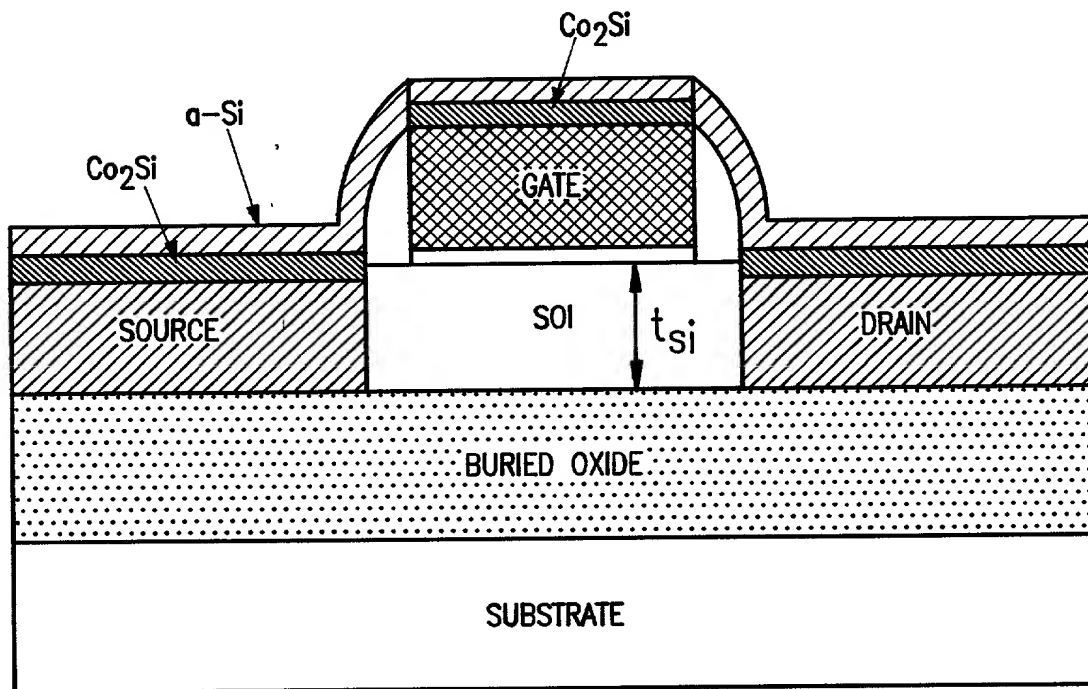


FIG.4

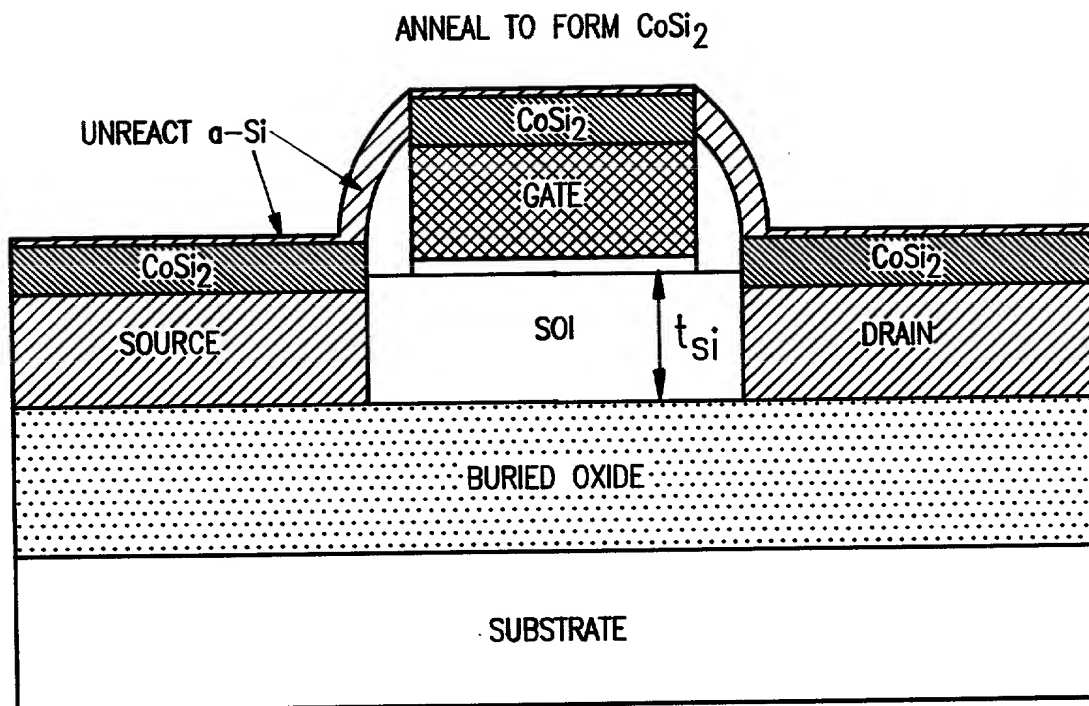


FIG.5

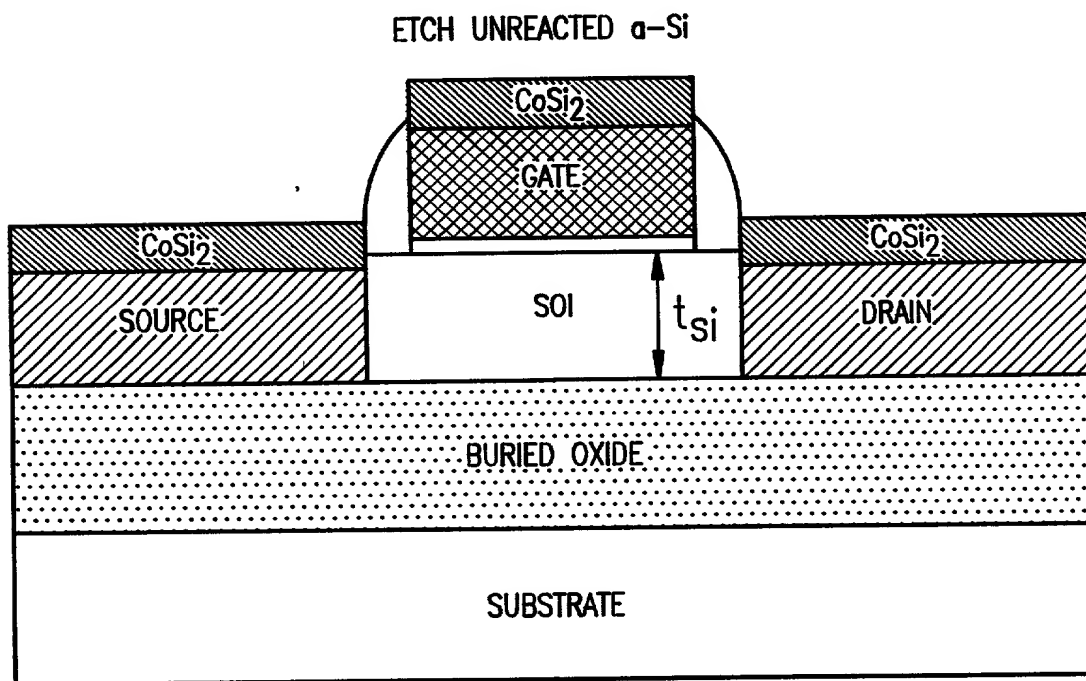


FIG.6

FIG.7A

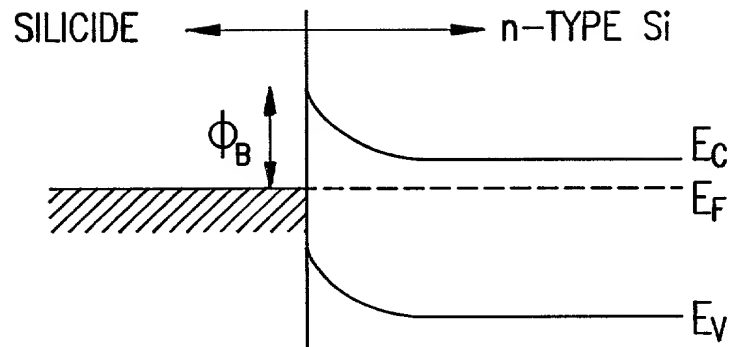
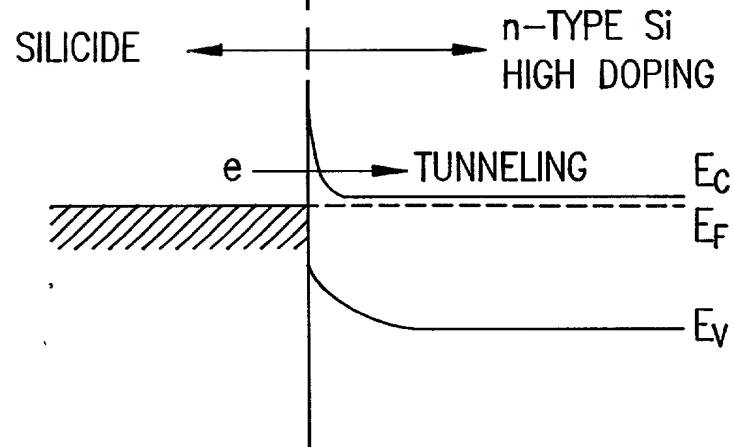
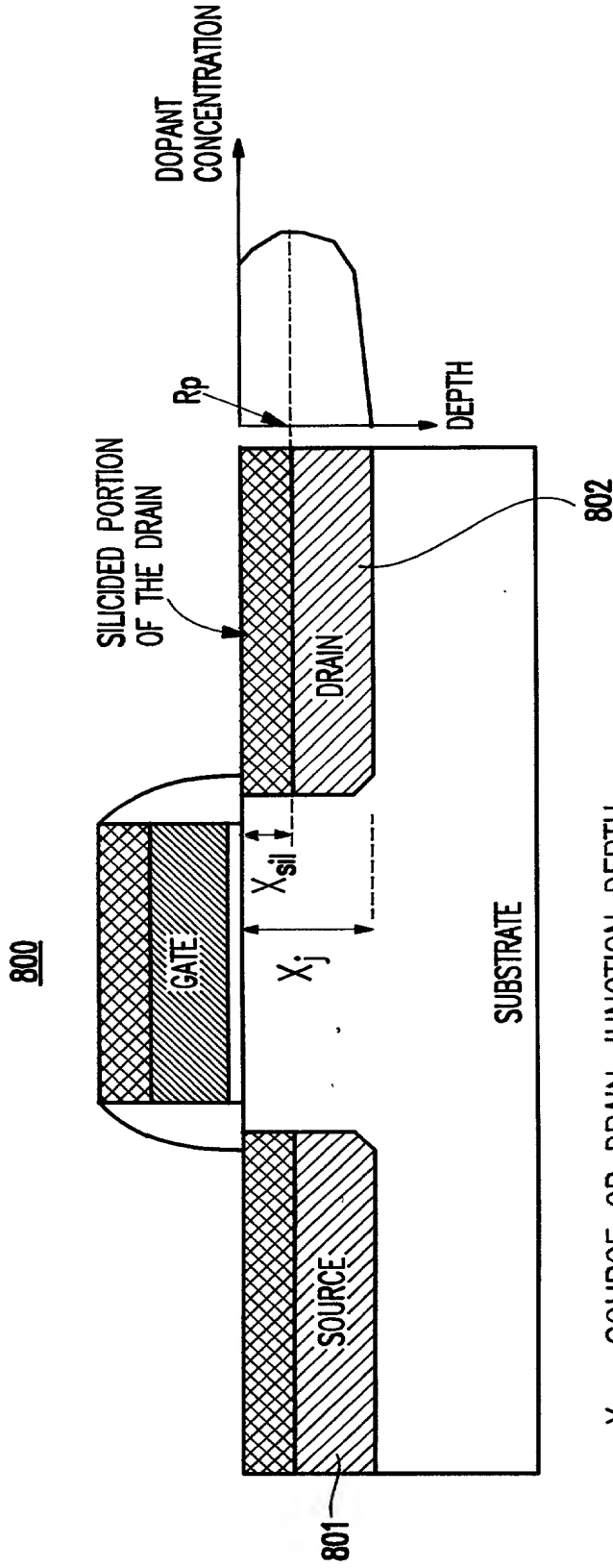


FIG.7B





$X_j$  = SOURCE OR DRAIN JUNCTION DEPTH

$X_{sil}$  = SILICIDE JUNCTION DEPTH

$R_p$  = PEAK DOPANT CONCENTRATION

REQUIREMENTS:

1.  $X_j > X_{sil}$
2.  $X_{sil}$  ROUGHLY EQUALS  $R_p$

FIG.8

